

## Product Summary

| $V_{(BR)DSS}$ | $R_{DS(on) \text{ max}}$               | $I_D$<br>$T_A = +25^\circ\text{C}$ |
|---------------|--|------------------------------------|
| 100V          | 220m $\Omega$ @ $V_{GS} = 10\text{V}$  | 2.24A                              |
|               | 250m $\Omega$ @ $V_{GS} = 4.5\text{V}$ | 2.10A                              |

## Description

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

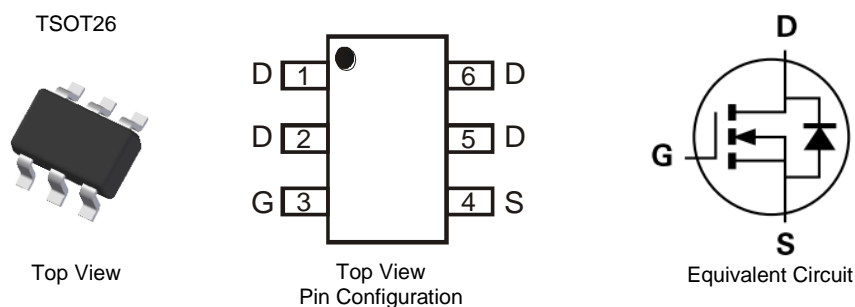
- DC-DC Converters
- Power Management Functions
- Backlighting

## Features and Benefits

- Low Input Capacitance
- Low On-Resistance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

## Mechanical Data

- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Tin Finish Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208(3)
- Weight: 0.013 grams (Approximate)

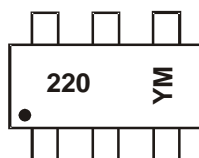


## Ordering Information (Note 4)

| Part Number     | Case   | Packaging          |
|-----------------|--------|--------------------|
| DMN10H220LVT-7  | TSOT26 | 3,000/Tape & Reel  |
| DMN10H220LVT-13 | TSOT26 | 10,000/Tape & Reel |

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



220 = Product Type Marking Code  
 YM = Date Code Marking  
 Y or  $\bar{Y}$  = Year (ex: C = 2015)  
 M = Month (ex: 9 = September)

### Date Code Key

| Year | 2015 | 2016 | 2017 | 2018 | 2019 | 2020 | 2021 | 2022 |
|------|------|------|------|------|------|------|------|------|
| Code | C    | D    | E    | F    | G    | H    | I    | J    |

| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
|-------|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|
| Code  | 1   | 2   | 3   | 4   | 5   | 6   | 7   | 8   | 9   | O   | N   | D   |

**Maximum Ratings** (@T<sub>A</sub> = +25°C unless otherwise specified.)

| Characteristic  | Symbol                          | Value | Units |
|---|---------------------------------|-------|-------|
| Drain-Source Voltage                                    | V <sub>DSS</sub>                | 100   | V     |
| Gate-Source Voltage                                     | V <sub>GSS</sub>                | ±16   | V     |
| Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V | (Note 6) T <sub>A</sub> = +25°C | 2.24  | A     |
|   | (Note 6) T <sub>A</sub> = +70°C | 1.79  | A     |
|   | (Note 5) T <sub>A</sub> = +25°C | 1.87  | A     |
|   | (Note 5) T <sub>A</sub> = +70°C | 1.50  | A     |
| Maximum Continuous Body Diode Forward Current (Note 6)  | I <sub>S</sub>                  | 1.50  | A     |
| Pulsed Drain Current (10μs pulse, duty cycle = 1%)      | I <sub>DM</sub>                 | 6.60  | A     |

**Thermal Characteristics** (@T<sub>A</sub> = +25°C unless otherwise specified.)

| Characteristic                          | Symbol                            | Value                  | Units |
|---|-----------------------------------|------------------------|-------|
| Total Power Dissipation (Note 6)        | P <sub>D</sub>                    | T <sub>A</sub> = +25°C | 1.67  |
|   |                                   | T <sub>A</sub> = +70°C | 1.07  |
| Thermal Resistance, Junction to Ambient | R <sub>θJA</sub>                  | (Note 6)               | 75    |
|   |                                   | (Note 5)               | 108   |
| Operating and Storage Temperature Range | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150            | °C    |

**Electrical Characteristics** (@T<sub>A</sub> = +25°C unless otherwise specified.)

| Characteristic                             | Symbol              | Min | Typ  | Max  | Unit | Test Condition   |
|--|---------------------|-----|------|------|------|--|
| <b>OFF CHARACTERISTICS (Note 7)</b>        |                     |     |      |      |      |  |
| Drain-Source Breakdown Voltage             | BV <sub>DSS</sub>   | 100 | —    | —    | V    | V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA   |
| Zero Gate Voltage Drain Current            | I <sub>DSS</sub>    | —   | —    | 1    | μA   | V <sub>DS</sub> = 100V, V <sub>GS</sub> = 0V   |
| Gate-Source Leakage                        | I <sub>GSS</sub>    | —   | —    | ±100 | nA   | V <sub>GS</sub> = ±16V, V <sub>DS</sub> = 0V   |
| <b>ON CHARACTERISTICS (Note 7)</b>         |                     |     |      |      |      |  |
| Gate Threshold Voltage                     | V <sub>GS(th)</sub> | 1   | 1.8  | 2.5  | V    | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA                                   |
| Static Drain-Source On-Resistance          | R <sub>DS(ON)</sub> | —   | 172  | 220  | mΩ   | V <sub>GS</sub> = 10V, I <sub>D</sub> = 1.6A   |
|  |                     |     | 211  | 250  |      | V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 1.3A  |
| Diode Forward Voltage                      | V <sub>SD</sub>     | —   | 0.77 | 1.2  | V    | V <sub>GS</sub> = 0V, I <sub>S</sub> = 1.1A  |
| <b>DYNAMIC CHARACTERISTICS (Note 8)</b>    |                     |     |      |      |      |  |
| Input Capacitance                          | C <sub>iSS</sub>    | —   | 401  | —    | pF   | V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V<br>f = 1MHz                                      |
| Output Capacitance                         | C <sub>oss</sub>    | —   | 22   | —    |      |  |
| Reverse Transfer Capacitance               | C <sub>rSS</sub>    | —   | 17   | —    |      |  |
| Gate Resistance                            | R <sub>g</sub>      | —   | 2.1  | —    | Ω    | V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz   |
| Total Gate Charge (V <sub>GS</sub> = 4.5V) | Q <sub>g</sub>      | —   | 4.1  | —    | nC   | V <sub>DS</sub> = 50V, I <sub>D</sub> = 1.6A   |
| Total Gate Charge (V <sub>GS</sub> = 10V)  | Q <sub>g</sub>      | —   | 8.3  | —    |      |  |
| Gate-Source Charge                         | Q <sub>gs</sub>     | —   | 1.5  | —    |      |  |
| Gate-Drain Charge                          | Q <sub>gd</sub>     | —   | 2    | —    |      |  |
| Turn-On Delay Time                         | t <sub>D(on)</sub>  | —   | 6.8  | —    | ns   | V <sub>DS</sub> = 50V, V <sub>GS</sub> = 4.5V,<br>R <sub>G</sub> = 6.8Ω, I <sub>D</sub> = 1A |
| Turn-On Rise Time                          | t <sub>r</sub>      | —   | 8.2  | —    |      |  |
| Turn-Off Delay Time                        | t <sub>D(off)</sub> | —   | 7.9  | —    |      |  |
| Turn-Off Fall Time                         | t <sub>f</sub>      | —   | 3.6  | —    |      |  |
| Reverse Recovery Time                      | t <sub>rr</sub>     | —   | 17   | —    | ns   | I <sub>F</sub> = 1.1A, di/dt = 100A/μs   |
| Reverse Recovery Charge                    | Q <sub>rr</sub>     | —   | 9.8  | —    |      |  |

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1-inch square copper plate.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to production testing.

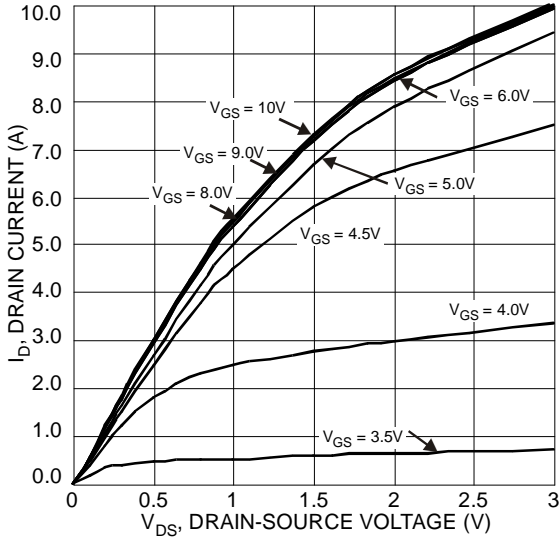


Figure 1 Typical Output Characteristic

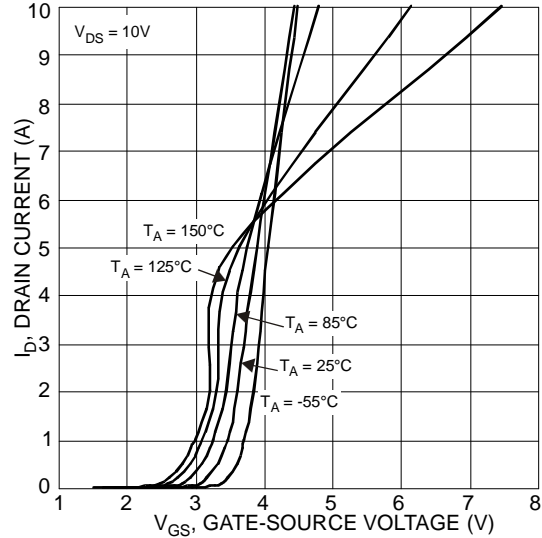


Figure 2 Typical Transfer Characteristics

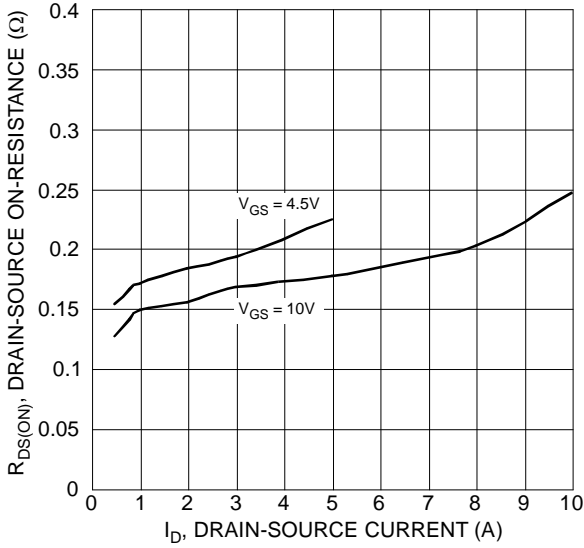


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

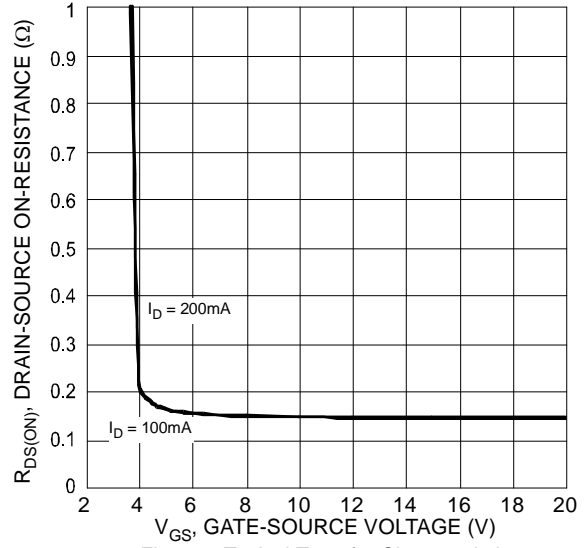


Figure 4 Typical Transfer Characteristic

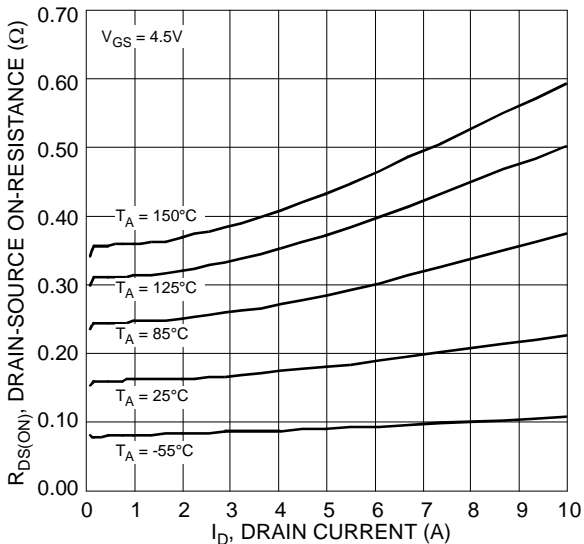


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

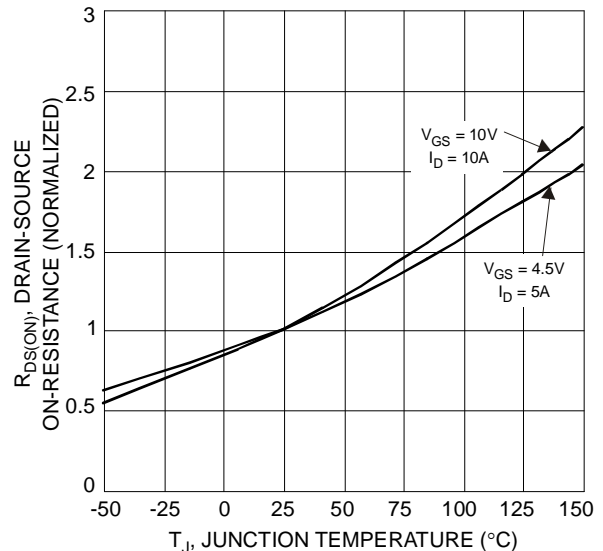


Figure 6 On-Resistance Variation with Temperature

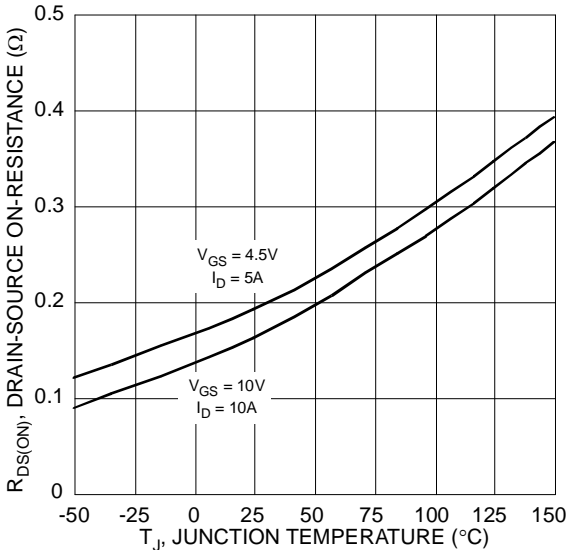


Figure 7 On-Resistance Variation with Temperature

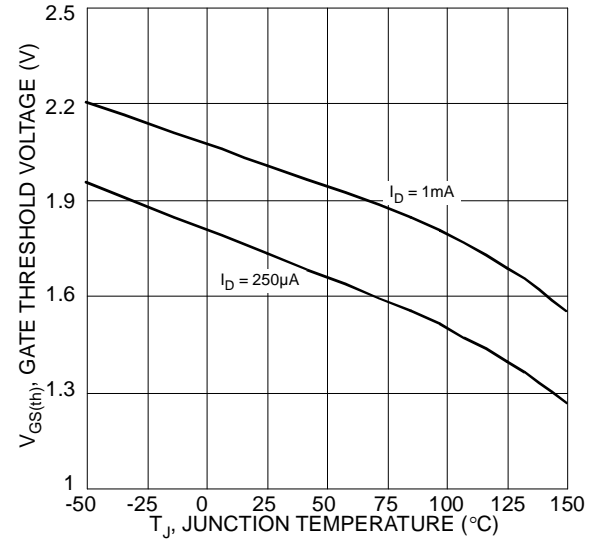


Figure 8 Gate Threshold Variation vs. Ambient Temperature

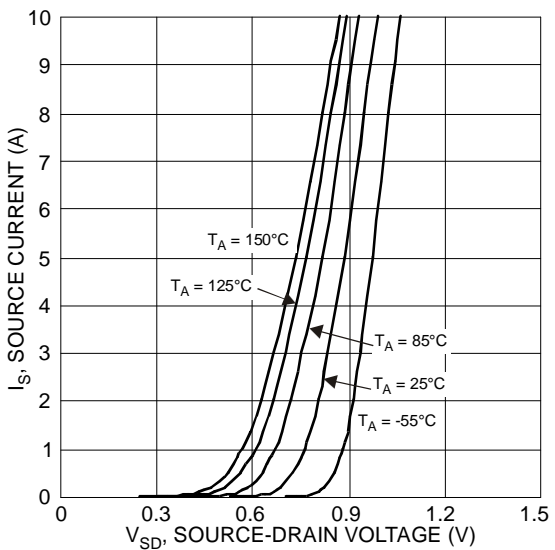


Figure 9 Diode Forward Voltage vs. Current

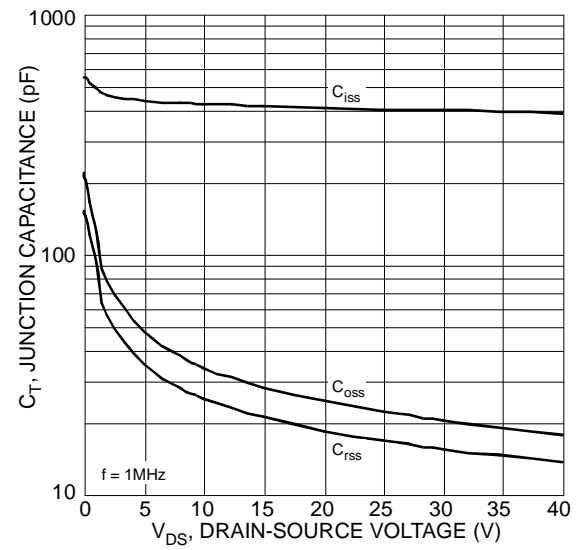


Figure 10 Typical Junction Capacitance

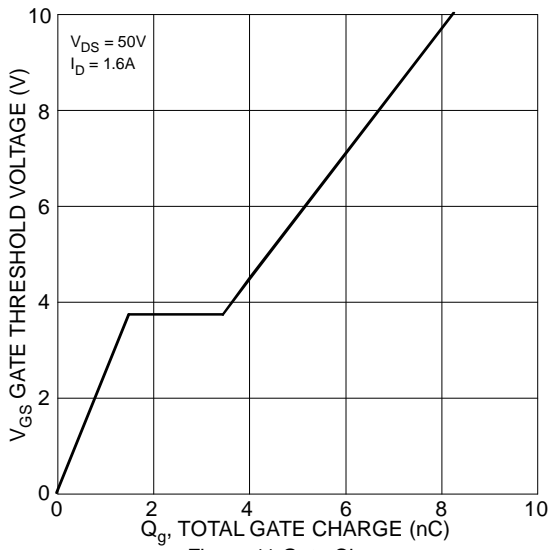


Figure 11 Gate Charge

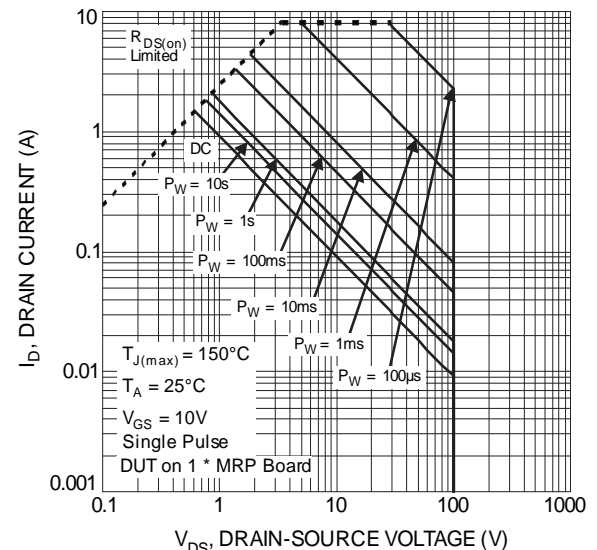


Figure 12 SOA, Safe Operation Area

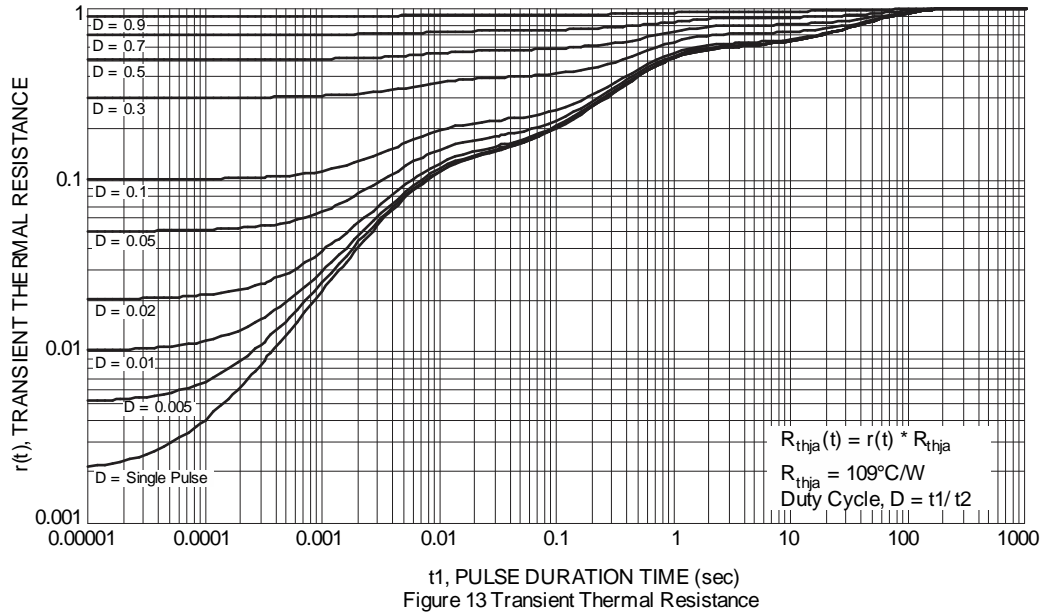
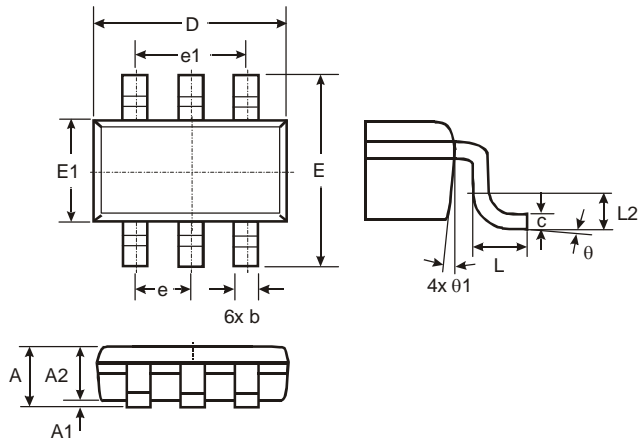


Figure 13 Transient Thermal Resistance

**Package Outline Dimensions**

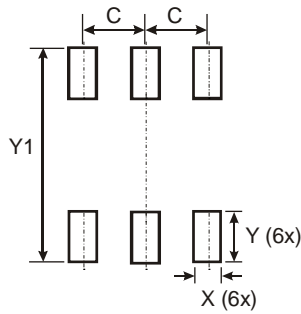
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



| TSOT26               |      |      |      |
|----------------------|------|------|------|
| Dim                  | Min  | Max  | Typ  |
| A                    | —    | 1.00 | —    |
| A1                   | 0.01 | 0.10 | —    |
| A2                   | 0.84 | 0.90 | —    |
| D                    | —    | —    | 2.90 |
| E                    | —    | —    | 2.80 |
| E1                   | —    | —    | 1.60 |
| b                    | 0.30 | 0.45 | —    |
| c                    | 0.12 | 0.20 | —    |
| e                    | —    | —    | 0.95 |
| e1                   | —    | —    | 1.90 |
| L                    | 0.30 | 0.50 | —    |
| L2                   | —    | —    | 0.25 |
| theta                | 0°   | 8°   | 4°   |
| theta1               | 4°   | 12°  | —    |
| All Dimensions in mm |      |      |      |

**Suggested Pad Layout**

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| C          | 0.950         |
| X          | 0.700         |
| Y          | 1.000         |
| Y1         | 3.199         |

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